



Form PTO 1449 (Rev. 10-2002)				U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. 034299-548		Serial No. 10/718,109	
Information Disclosure Statement by Applicant						Applicant: Mazen et al			
(Use several sheets if necessary)						Filed: 11/19/03		Group: Unassigned	
U.S. Patent Documents									
Init.		Document No.	Date	Name	Class	Subclass	Filing Date		
m	A	5,250,452	10/93	Ozturk et al					
m	B	US 2003/0186512	10/03	Semeria et al					
Other Documents (Including Author, Title, Date, Pertinent Pages, etc.)									
m	C	Copy of French Search Report, corresponding to French patent application FR 0214658							
	D	Madhukar, et al "CVD growth of Si nanocrystals on dielectric surfaces for nanocrystal floating gate memory application, Mat. Res. Soc. Symp. Proc. Vol. 638 © 2001 Material Research Society							
	E	Fernandes et al, "Memory Characteristics of Si Quantum Dot Devices with SiO ₂ /ALD AL ₂ O ₃ Tunneling Dielectrics							
	F	Mazen et al, "A two Steps CVD process for the growth of Silicon nano-crystals, Applied Surface Science 214 (2003) 359-363							
	G	Schmidt et al, "Self-Assembled Ge/Si Dots for Faster Field-Effect Transistors, IEEE Transactions on Electron Devices, Vol. 48, No. 6, 6-01							
	H	Kamins et al, "Lithographic positioning of self-assembled Ge islands on Si(001) © 1997 American Institute fo Physics							
	I	Baron et al, "Silicon quantum dot nucleation on Si ₃ N ₄ , SiO ₂ and SiO _x N _y substrates for nanoelectronic devices, Journal of Crystal Growth 209 (2000) 1004-1008							
m	J	Ishii et al, "Selective Ge deposition on Si using thermal decomposition of GeH ₄ , © 1985 American Institute of Physics							

Examiner	Kuo Hoang					Date Considered 3-2-05			
Examiner: Initial if citation considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include a copy of this form with the next communication to applicant.									